

Description

The HSTD30PF03LT4 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

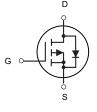


TO-252-2L

General Features

 $V_{DS} = -30V I_{D} = -40A$

 $R_{DS(ON)}$ < 23 m Ω @ V_{GS} =10V



P-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HSTD30PF03LT4	TO-252-2L	HXY MOSFET	2500

Absolute Maximum Ratings (T_c=25[°]Cunless otherwise noted)

Symbol	Symbol Parameter		Units		
VDS	Drain-Source Voltage	-30	V		
VGS	Gate-Source Voltage	Gate-Source Voltage ±20			
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	А			
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	Continuous Drain Current, V _{GS} @ 10V ¹ -25			
IDM	Pulsed Drain Current ²	Pulsed Drain Current ² -70			
P _D @T _C =25°C	Total Power Dissipation ⁴	Total Power Dissipation ⁴ 34.7			
TSTG	Storage Temperature Range -55 to 150		°C		
TJ	Operating Junction Temperature Range -55 to 150		°C		
R₀JA	Thermal Resistance Junction-ambient ¹	nt ¹ 62			
R _θ JC	Thermal Resistance Junction-Case ¹ 3.6		°C/W		



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V_{GS} =0V , I_D =-250uA	-30			V
$\triangle BV_{DSS}/\triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =-1mA		-0.022		V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-15A		18	23	mΩ
		V _{GS} =-4.5V , I _D =-10A		37	44	
V _{GS(th)}	Gate Threshold Voltage	\\ _\\ _ 050\	-1.0		-2.5	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	─_V _{GS} =V _{DS} , I _D =-250uA		4.6		mV/°C
	Duning Courses Londons Cummont	V _{DS} =-24V , V _{GS} =0V , T _J =25°C			-1	
IDSS	Drain-Source Leakage Current	V _{DS} =-24V , V _{GS} =0V , T _J =55°C			-5	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-10A		5		S
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		13		Ω
Qg	Total Gate Charge (-4.5V)			12.5		
Q_{gs}	Gate-Source Charge	V _{DS} =-15V , V _{GS} =-4.5V , I _D =-15A		5.4		nC
Q _{gd}	Gate-Drain Charge			5		
T _{d(on)}	Turn-On Delay Time			4.4		
Tr	Rise Time	V_{DD} =-15V , V_{GS} =-10V , R_{G} =3.3 Ω ,		11.2		
T _{d(off)}	Turn-Off Delay Time	I _D =-15A		34		ns
T _f	Fall Time			18		
Ciss	Input Capacitance			1345		
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		194		pF
C _{rss}	Reverse Transfer Capacitance			158		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	-	-	-40	Α
I _{SM}	Pulsed Source Current ^{2,5}	VG-VD-0V , Force Current			-75	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C			-1.2	V
t _{rr}	Reverse Recovery Time	IF=-15A , dI/dt=100A/μs ,		12.4		nS
Qrr	Reverse Recovery Charge	T _J =25°C		5		nC

Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%
- 3. The EAS data shows Max. rating . The test condition is V_{DD} =-25V, V_{GS} =-10V,L=0.1mH, I_{AS} =-38A
- 4. The power dissipation is limited by 150°C junction temperature
- 5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

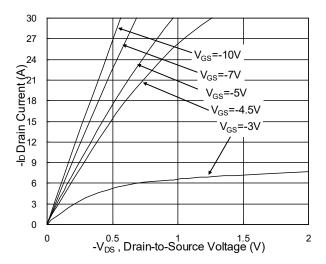


Fig.1 Typical Output Characteristics

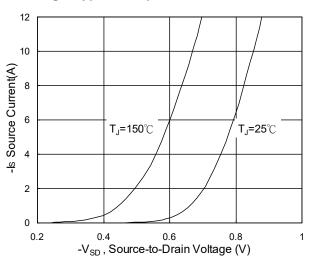


Fig.3 Forward Characteristics of Reverse

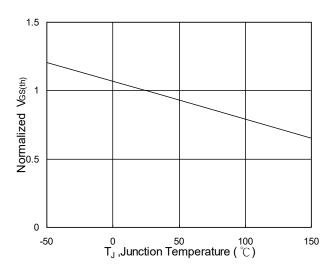


Fig.5 Normalized V_{GS(th)} v.s T_J

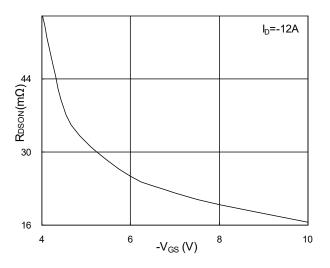


Fig.2 On-Resistance v.s Gate-Source

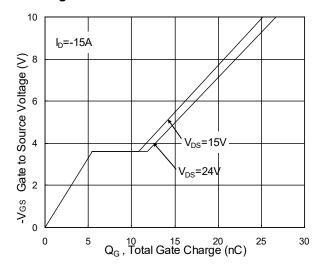


Fig.4 Gate-Charge Characteristics

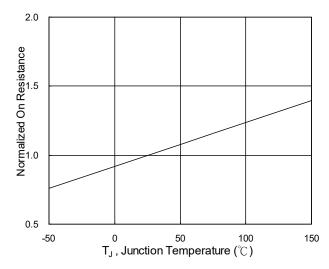
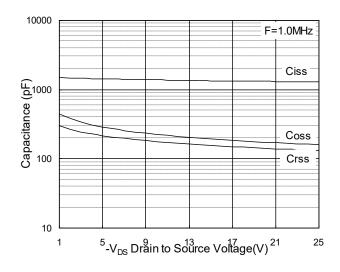


Fig.6 Normalized R_{DSON} v.s T_J



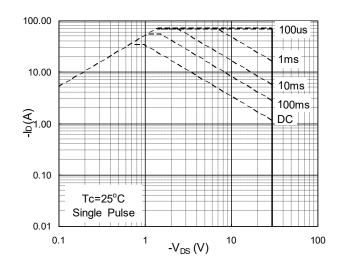


Fig.7 Capacitance

Fig.8 Safe Operating Area

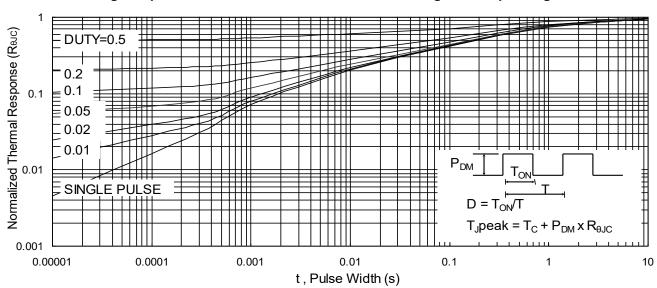


Fig.9 Normalized Maximum Transient Thermal Impedance

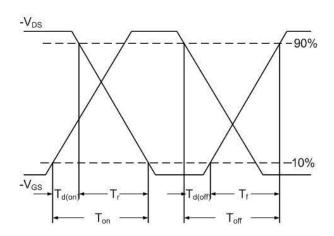


Fig.10 Switching Time Waveform

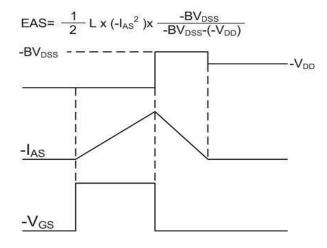
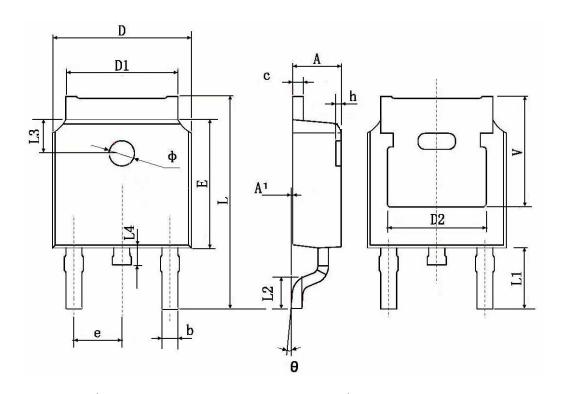


Fig.11 Unclamped Inductive Switching Waveform



TO-252-2L Package Information



0	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900	2.900 TYP.		TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.600	TYP.	0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	TYP.	0.211 TYP.		



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